

D. J. SANGHVI COLLEGE OF ENGINEERING
DEPARTMENT OF ELECTRONICS ENGINEERING
EXL302: ELECTRONIC DEVICES AND CIRCUITS 1 SEM III
MID TERM 1

9th September, 2017

[Total Marks: 20]

1. Attempt all the questions for 20 marks
2. Read the questions carefully before attempting
3. Don't rewrite the question while answering, only answers have to be written.

Given: $n_i = 1.5 \times 10^{10}/cm^3$, $\epsilon_s = 10^{-12}F/cm$, $\frac{KT}{q} = 0.026V$, $q = 1.6 \times 10^{-19} C$

1. For a Si uniformly doped PN junction, acceptor doping concentration $N_A = 10^{17}/cm^3$ and donor doping concentration $N_D = 10^{18}/cm^3$ at $T=300K$
 - a) Calculate the built-in potential (V_{bi}) for the junction under zero-applied bias. [1]
 - b) Now calculate the depletion region width (W) and maximum E-field (E_m) for the junction. [1]
 - c) Draw energy band diagram of a pn junction in reverse bias. In the diagram, show barrier potential energy, energy band-gap, space-charge width and applied reverse voltage. [1]
 - d) Consider the energy band diagram shown below in figure 1, and then answer the following questions:

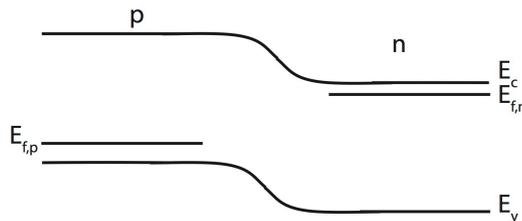


Figure 1: Question 1 d)

- i) The given EBD is for forward bias or reverse bias? [0.5]
- ii) What is the direction of electron diffusion and hole drift? [0.5]
- e) Two students were performing zener regulator experiment. They got the readings for variations in the line regulation as follows:

	Student A	Student B
$V_{PS}(Volts)$	$V_L(volts)$	$V_L(volts)$
10	6.415	6.252
11	6.420	6.325
12	6.421	6.545
13	6.425	6.785
14	6.432	6.995

- Among the students A and student B, which regulator do you think is showing better results and why? [1]

2. a) For the given clipper circuit in figure 2, draw the output waveforms for [2]
 i) Ideal diode model ii) constant voltage model

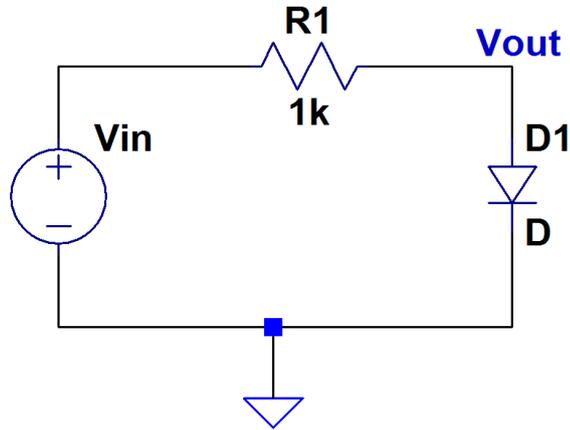


Figure 2: Question 2a

- b) For a N-channel JFET, starting from Shockley's equation, derive an expression [1]
 for transconductance (g_m)
- c) For an N-channel JFET, find drain current I_D if $I_{DSS} = 8mA$, $V_{GS} = -1V$ and [1]
 $V_P = -3V$
- d) Draw transfer characteristics of Enhancement type and depletion type N-channel [1]
 MOSFET

3. Consider the circuit in figure 3

✖ Input ac voltage is 120V r.m.s, 60 Hz

- a) What type of circuit is this [0.5]
 b) What is the total peak secondary voltage (i.e V_m) [0.5]
 c) Sketch the rectified output waveforms [1]
 d) Sketch the filtered output waveforms [1]
 e) What is the peak current through each diode (i.e I_m) [1]
 f) What is the PIV rating for each diode [1]

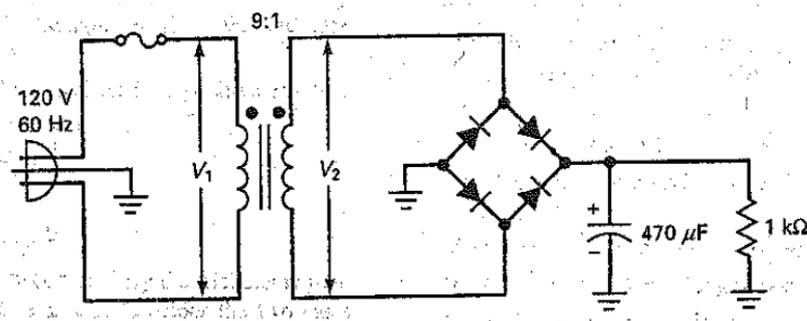


Figure 3: Question 3

4. Design a Full-wave center tapped rectifier employing an LC filter to meet the following [5] specifications:

i) Output dc voltage: 12V

ii) Load current (max): 500mA

iii) Ripple voltage $< 60\text{mV}$

✕ Specify ratings of the circuit components such as transformer, diode, choke, capacitors and resistors.
